

FIG. 1

Form STI by forming openings for STI regions, filling the openings with oxide S11 film and planarizing the surface by CMP Form polysilicon gate electrode by S12 depositing polysilicon film and etching and patterning the film Implant p- or n-type dopant ions **S13** into substrate to definesource/drain regions Form anti-silicidation film by depositing oxide or nitride film S20 and etching and patterning the film **S14** Silicidation S15 Form metal interconnects



FIG. 2

<u>S20</u>

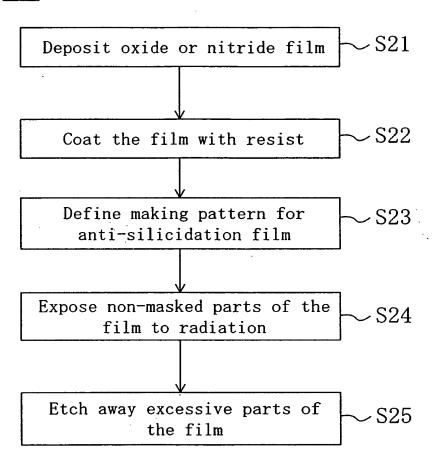




FIG. 3A

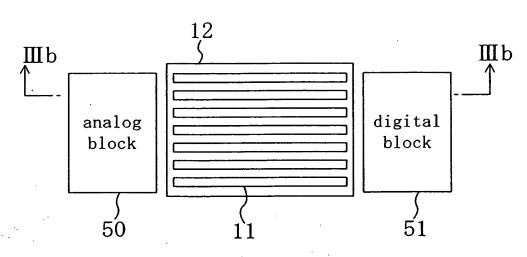
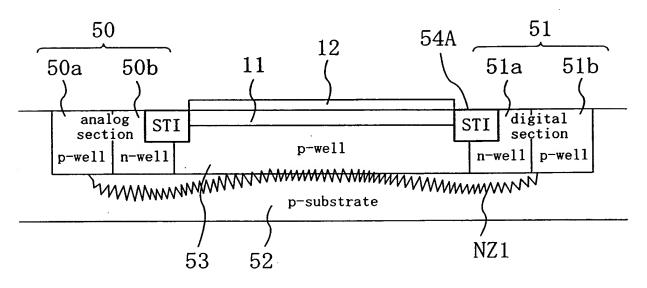
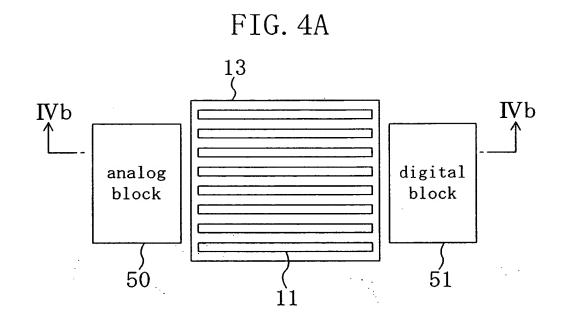


FIG. 3B







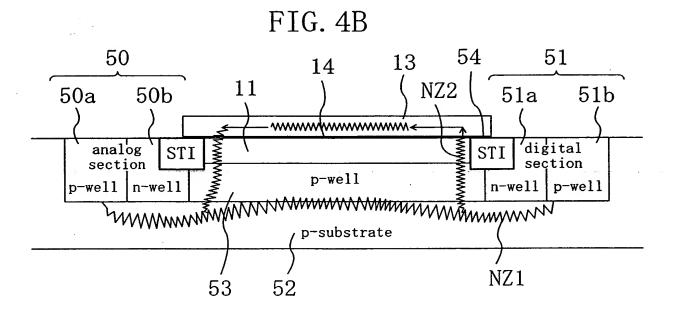




FIG. 5A

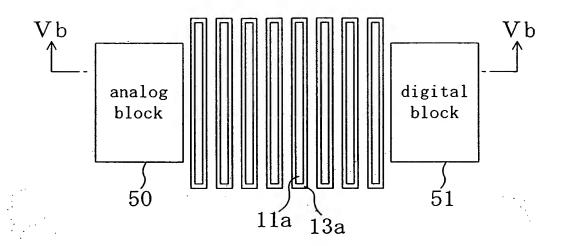
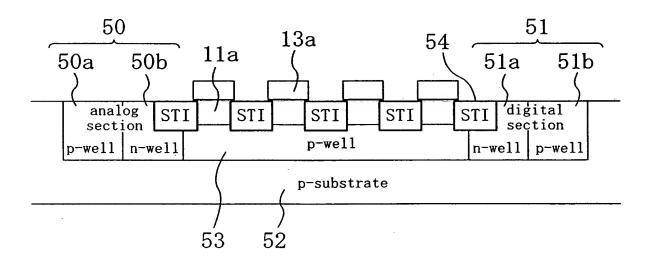
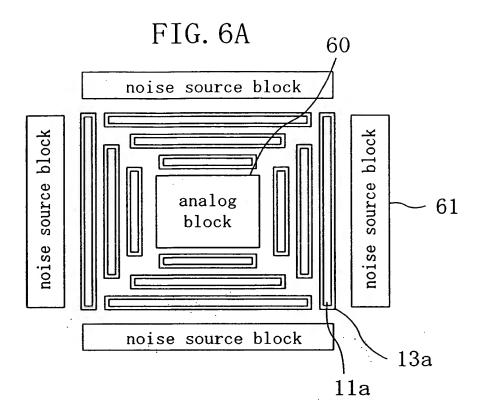


FIG. 5B







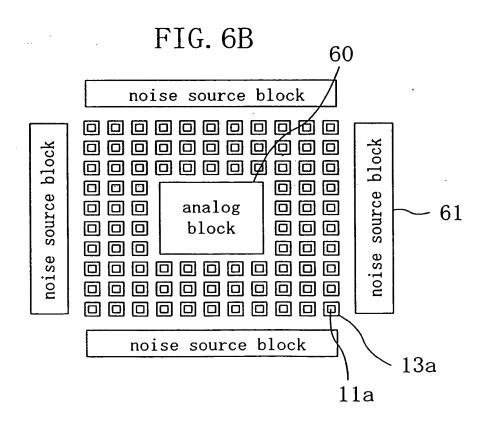




FIG. 7A

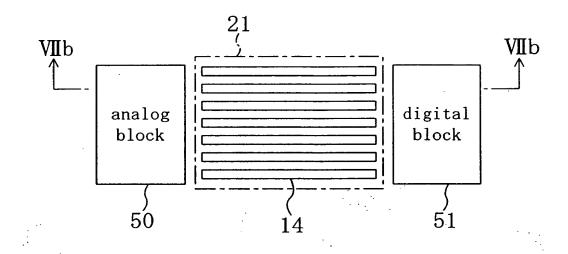


FIG. 7B

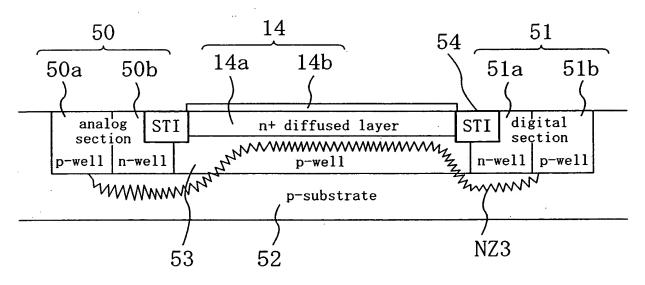




FIG. 8

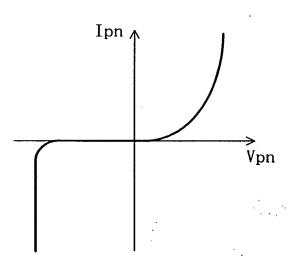


FIG. 9

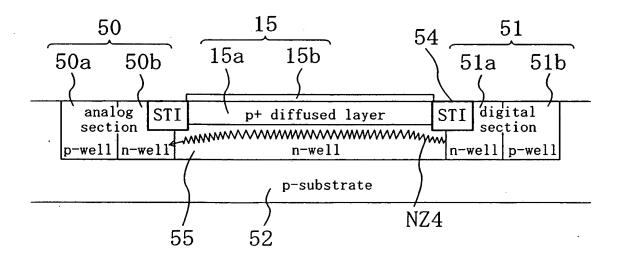


FIG. 10A

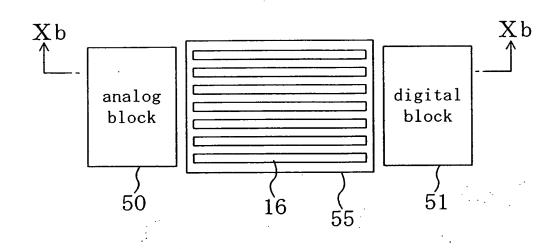


FIG. 10B

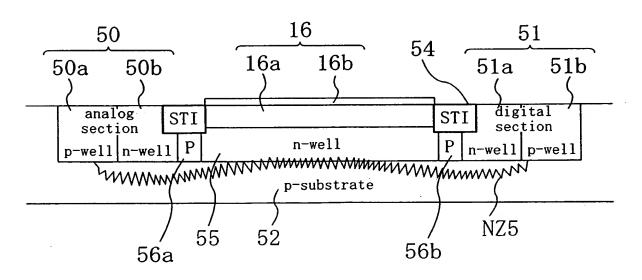




FIG. 11

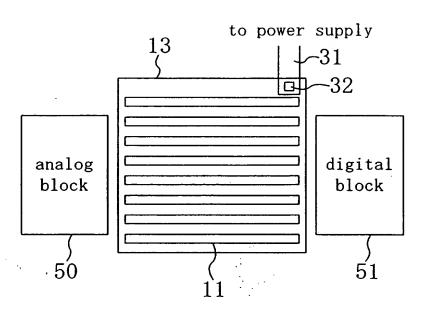


FIG. 12

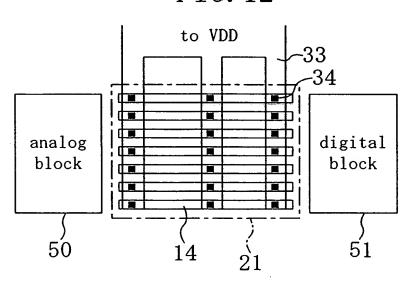


FIG. 13

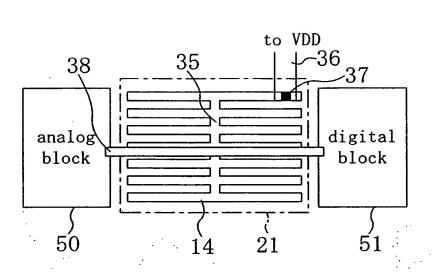




FIG. 14A

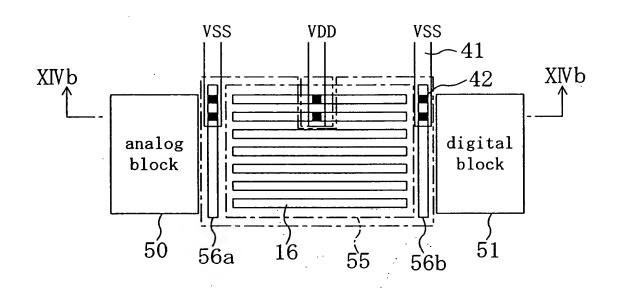


FIG. 14B

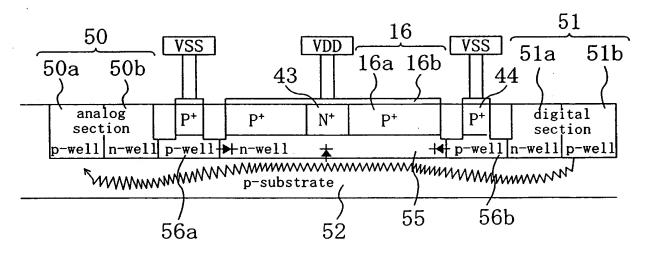
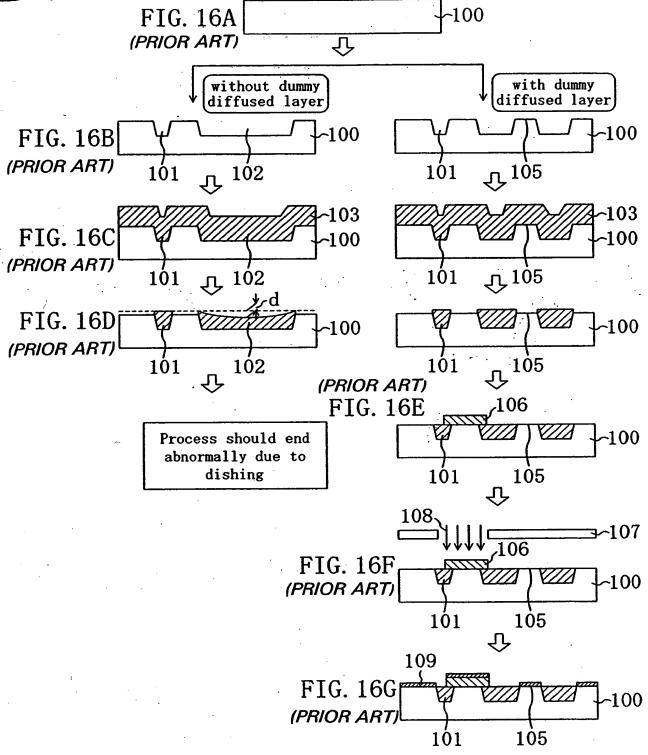




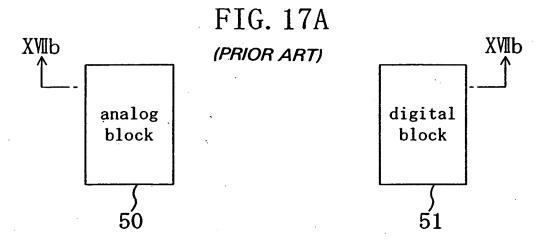
FIG. 15 (PRIOR ART)

Form STI by forming openings for STI regions, filling the openings with oxide film and planarizing the surface by CMP
Form polysilicon gate electrode by depositing polysilicon film and etching and patterning the film
Implant p- or n-type dopant ions into substrate to definesource/drain regions
Silicidation S14
Form metal interconnects \$15

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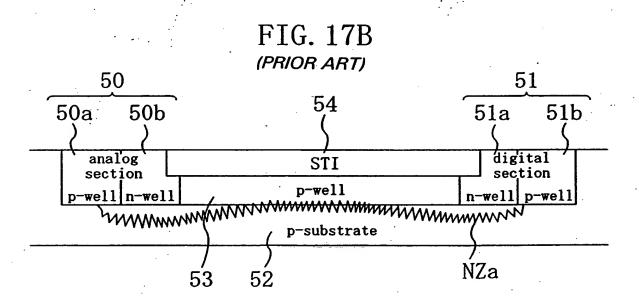




FIG. 18A

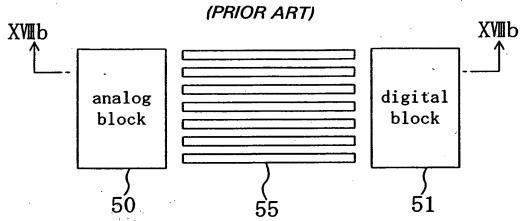


FIG. 18B (PRIOR ART)

